

IN THE SPECIFICATION:

Please replace paragraph [0026] with the following amended paragraph:

[0026] The heater plate 304 generally has a large mass compared to the substrate being processed in the system, and is generally fabricated from a material such as silicon carbide, quartz, or other materials that do not react with ambient gases in the RTA chamber 211 or with the substrate material. The heater 307 typically includes a resistive heating element or a conductive/radiant heat source and is disposed between heater plate 304 and a lift plate 328. The heater 307 is electrically coupled to a power source 316 which supplies the energy needed to heat the heater 307. A thermocouple 320 may be positioned in a conduit 322, disposed through the base 308 and dish 314, and extend into the heater plate 304 for the purpose of monitoring the annealing temperature. The thermocouple 320 may be connected to a controller 392, and therefore supply temperature measurements thereto. Controller 392 may then increase or decrease the heat supplied by the heater 307 according to the temperature measurements and a desired ~~adesired~~ anneal temperature.

Please replace paragraph [0029] with the following amended paragraph:

[0029] The substrate support pins 306 generally include distally tapered members constructed from quartz, aluminum oxide, silicon carbide, or other high temperature resistant materials. Each substrate support pin 306 is disposed within a tubular conduit 326, typically made of a heat and oxidation resistant material, that extends through the heater plate 304. The substrate support pins 306 are connected to the lift plate 328 for moving the substrate support pins 306 in a uniform manner. The lift plate 328 is attached to an ~~to an~~ actuator 330, such as a stepper motor, through a lift shaft 332 that moves the lift plate 328 to facilitate positioning of a substrate at various vertical positions within the RTA chamber 211. The lift shaft 332 extends through the base 308 of the enclosure 302 and is sealed by a sealing flange 334 disposed around the shaft.

Please replace paragraph [0042] with the following amended paragraph:

[0042] Etching of the dielectric layer 14 may be accomplished with any dielectric etching process, including plasma etching. Specific chemical etchants used to etch dielectrics such as silicon dioxide or organic dielectric materials may include such chemical etchants as as buffered hydrofluoric acid or acetone. However, patterning and etching may be accomplished using any method known in the art. The substrate 12 may be a layer, wire or device comprising a metal, doped silicon or other conductive material.